

2N7002H 60 V, N-channel Trench MOSFET 1 December 2021

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- · Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Table II dalon							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	360	mA
Static characte	eristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 500 mA; T _j = 25 °C		-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	
2	S	source		
3	D	drain		G mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
2N7002H	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
2N7002H	M9%

[1] % = placeholder for manufacturing site code

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8. Limiting values

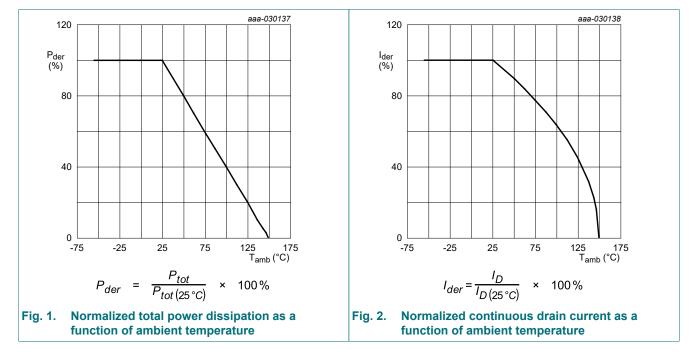
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

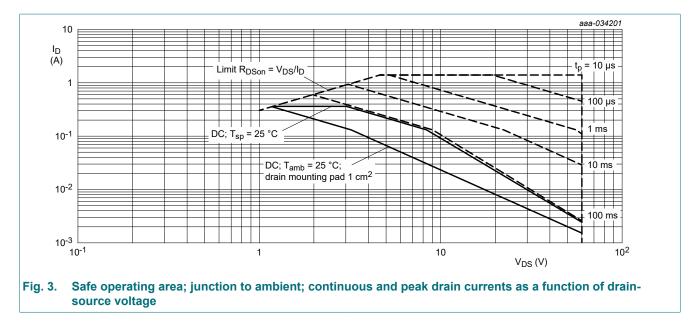
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V _{GS}	gate-source voltage	_		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	360	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	230	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	1.4	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	340	mW
			[1]	-	420	mW
		T _{sp} = 25 °C		-	1.1	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
Is	source current	T _{amb} = 25 °C	[1]	-	360	mA

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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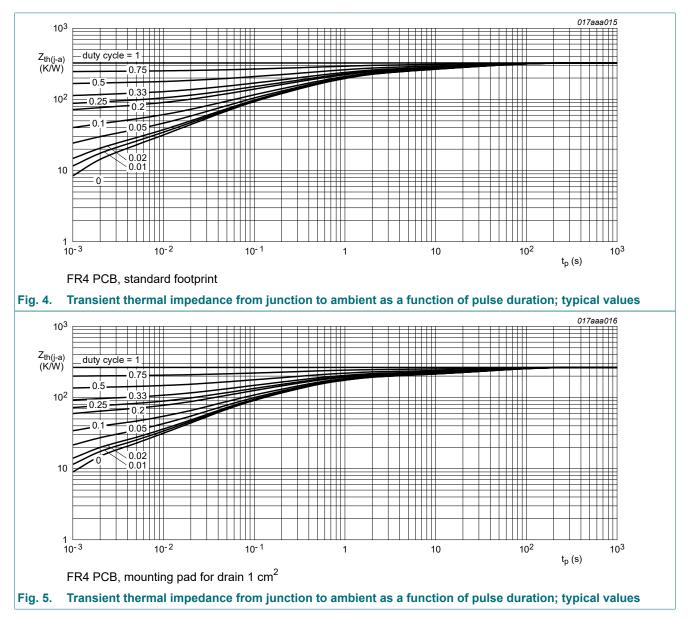
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9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-a)	thermal resistance from	in free air	[1]	-	310	370	K/W
	junction to ambient		[2]	-	260	300	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



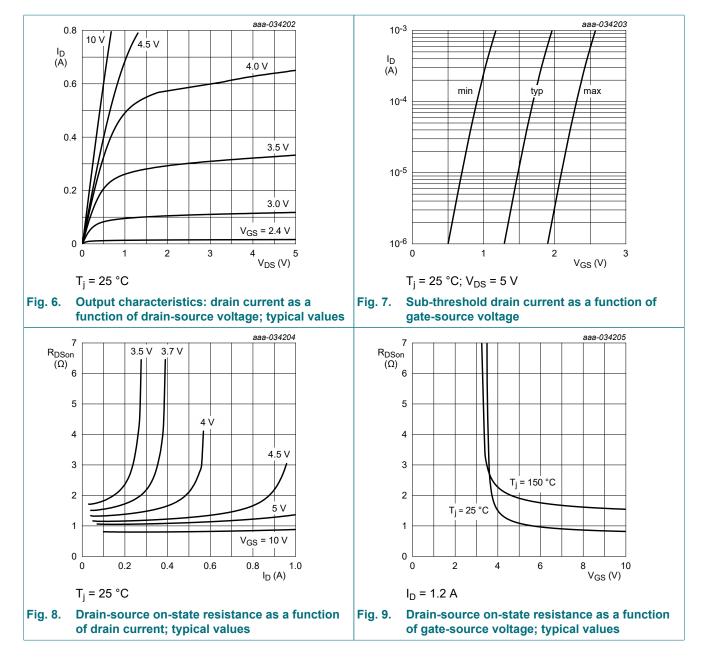
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics		I			
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 10 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	1.1	1.75	2.4	V
I _{DSS} dr	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS} gate leakage curren	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon} drain-source on-stat resistance	drain-source on-state	V _{GS} = 10 V; I _D = 500 mA; T _j = 25 °C	-	1	1.6	Ω
	resistance	V _{GS} = 10 V; I _D = 500 mA; T _j = 150 °C	-	2.1	3.3	Ω
		V _{GS} = 5 V; I _D = 50 mA; T _j = 25 °C	-	1.3	2	Ω
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	400	-	mS
Dynamic ch	aracteristics		I			
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 300 mA; V _{GS} = 4.5 V;	-	0.3	0.5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q _{GD}	gate-drain charge	1	-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	34	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 50 V; R _L = 250 Ω; V _{GS} = 10 V;	-	2	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	3	-	ns
t _{d(off)}	turn-off delay time	1 – – – – – – – – – – – – – – – – – – –	-	6	-	ns
t _f	fall time] [-	4	-	ns
Source-drai	n diode	· ·				
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.75	1.1	V

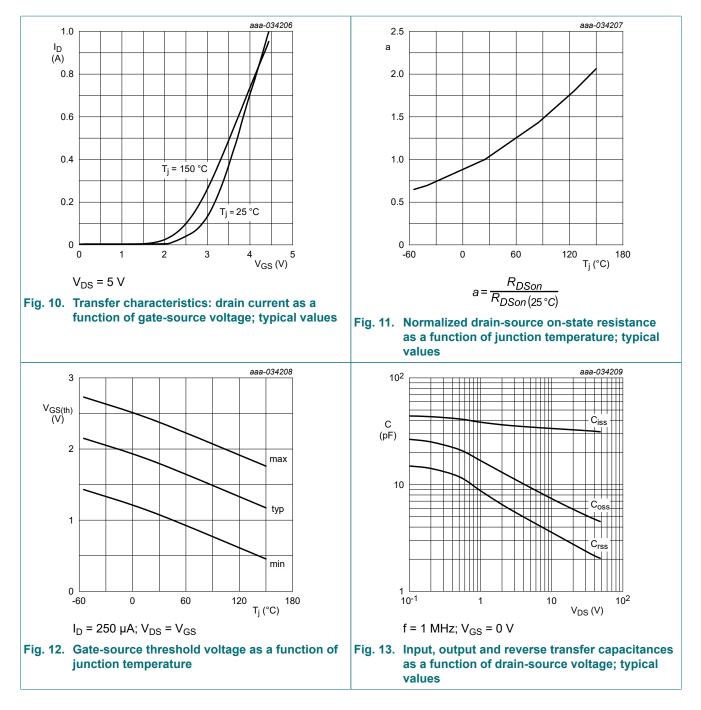
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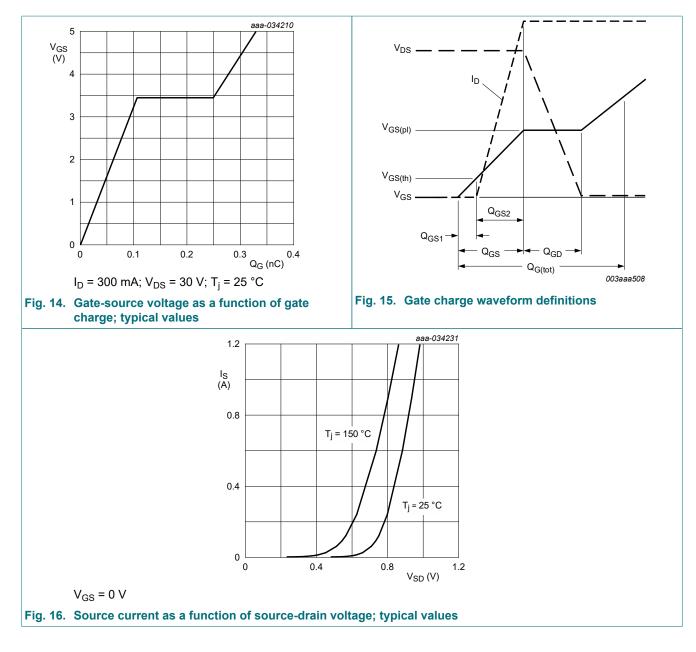
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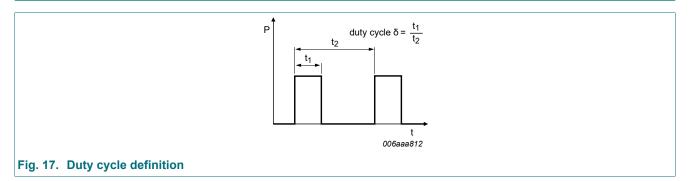
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11. Test information

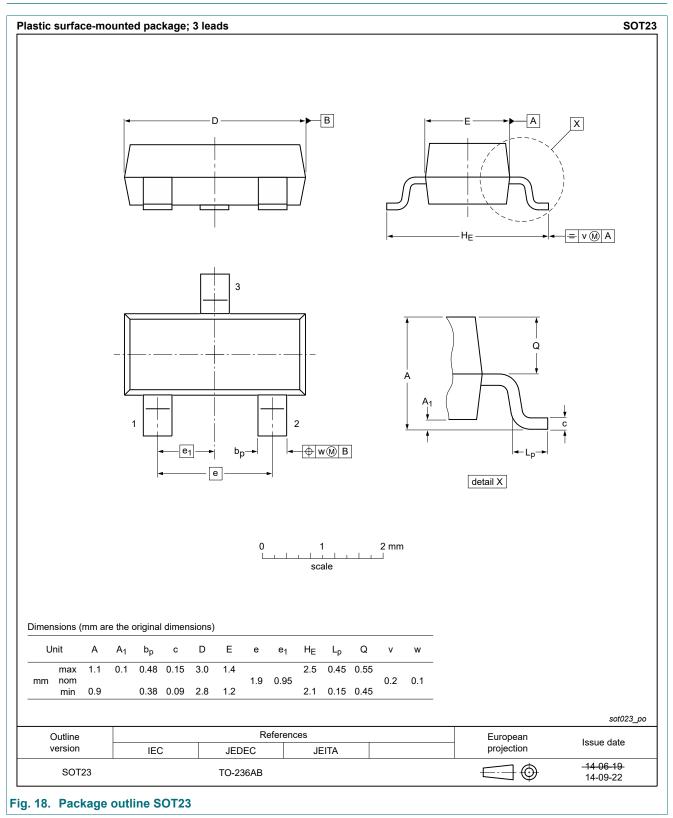


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

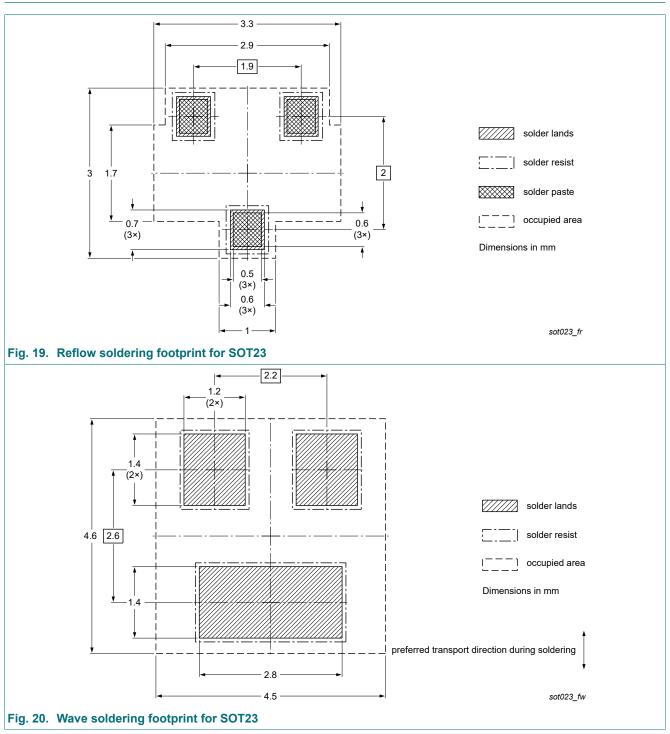
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
2N7002H v.2	20211201	Product data sheet	-	2N7002H v.1			
Modifications:	Changed document	Changed document status to "Product data sheet"					
2N7002H v.1	20211119	Preliminary data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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